IN THE CLAIMS

1. (original) A method of generating a deep N-well pattern for an integrated circuit design, said method comprising:

specifying a tile comprising a first layer wherein said first layer comprises a first layer element for a deep N-well pattern;

arranging multiple instances of said tile to create a tile array covering a portion of said integrated circuit design; and

merging said tiles to produce a deep N-well pattern.

- 2. (original) The method of Claim 1, wherein said tile further comprises a second layer, wherein said second layer comprises a second layer element.
- 3. (original) The method of Claim 2, wherein said first layer element is identical in shape to said second layer element.
- 4. (original) The method of Claim 3, wherein said first layer element is disposed rotated with respect to said second layer element.
- 5. (original) The method of Claim 1, further comprising editing said tile array.

Claims 6-7 (canceled) (restriction)

8. (original) The method of Claim 2, further comprising flattening said first layer and said second layer.

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Claims 9-24 (canceled) (restriction)

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